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1 Description

The M24M01 is a 1 Mb I²C-compatible EEPROM (Electrically Erasable PROgrammable Memory) organized as 128 K × 8 bits.

The M24M01-R can operate with a supply voltage from 1.8 V to 5.5 V, and the M24M01-DF can operate with a supply voltage from 1.7 V to 5.5 V, over an ambient temperature range of -40 °C / +85 °C.

The M24M01-D offers an additional page, named the Identification Page (256 bytes). The Identification Page can be used to store sensitive application parameters which can be (later) permanently locked in Read-only mode.

Figure 1. Logic diagram

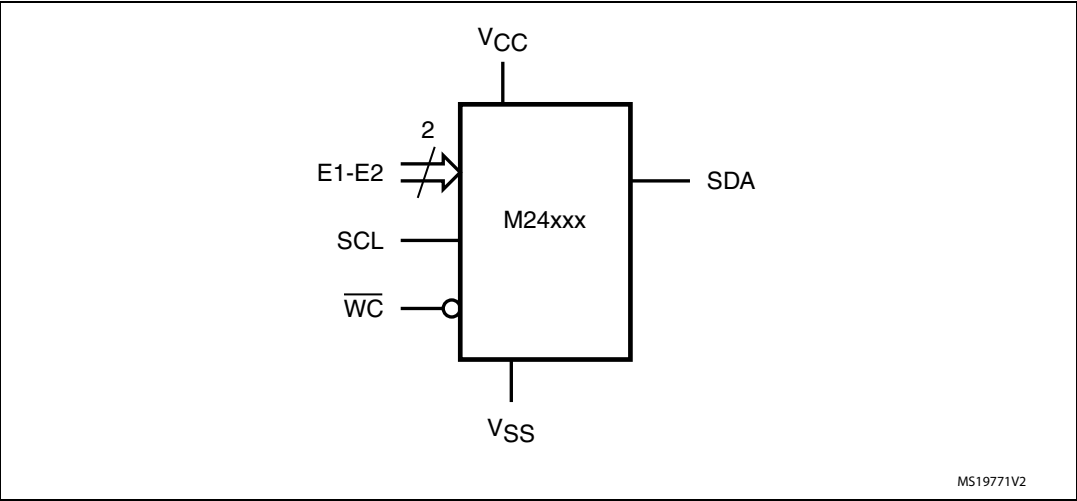
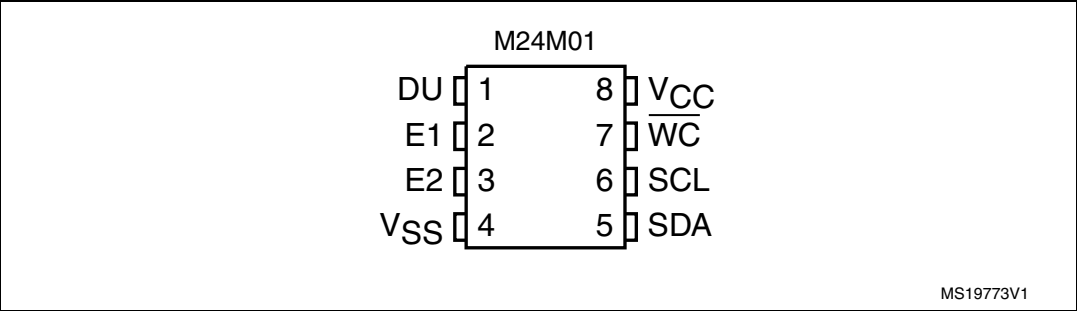


Table 1. Signal names

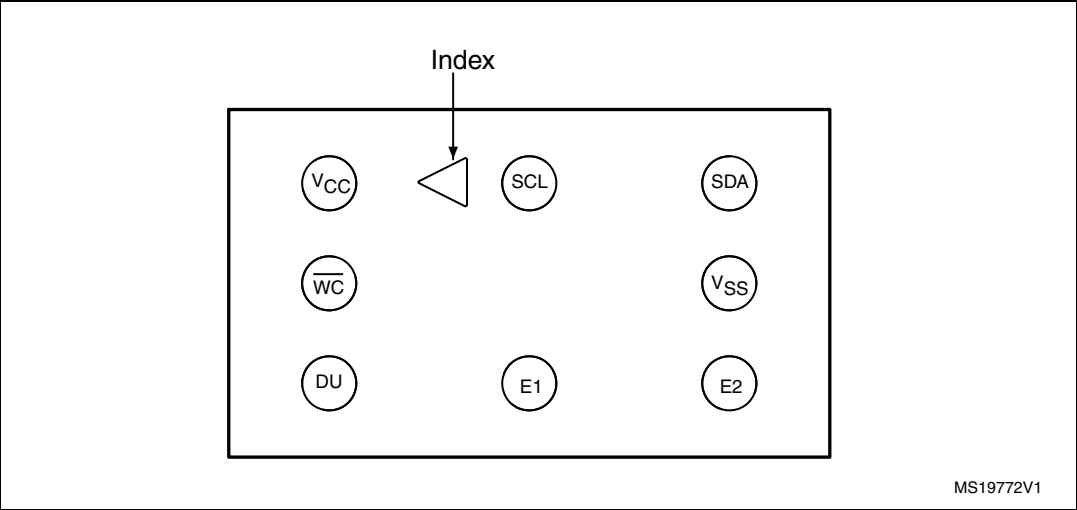
Signal name	Function	Direction
E1, E2	Chip Enable	Input
SDA	Serial Data	I/O
SCL	Serial Clock	Input
WC	Write Control	Input
V _{CC}	Supply voltage	
V _{SS}	Ground	

Figure 2. 8-pin package connections



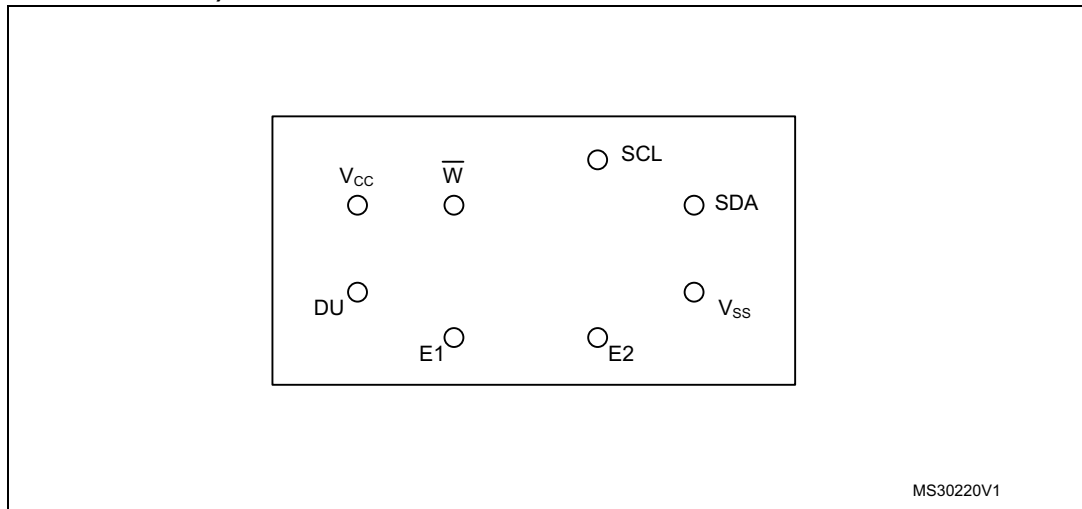
- 1. DU: Don't Use (if connected, must be connected to VSS)
- 2. See [Section 9: Package mechanical data](#) for package dimensions, and how to identify pin 1.

Figure 3. WLCSP connections for die identified by process letter A (bump side view)



- 1. DU: Don't Use (if connected, must be connected to VSS)
- 2. See [Section 9: Package mechanical data](#) for package dimensions, and how to identify pin 1.

Figure 4. WLCSP connections for die identified by process letter K (bump side view)



1. DU: Don't Use (if connected, must be connected to V_{SS})
2. See [Section 9: Package mechanical data](#) for package dimensions, and how to identify pin 1.

Caution: As EEPROM cells lose their charge (and so their binary value) when exposed to ultra violet (UV) light, EEPROM dice delivered in wafer form by STMicroelectronics must never be exposed to UV light.

2 Signal description

2.1 Serial Clock (SCL)

The signal applied on the SCL input is used to strobe the data available on SDA(in) and to output the data on SDA(out).

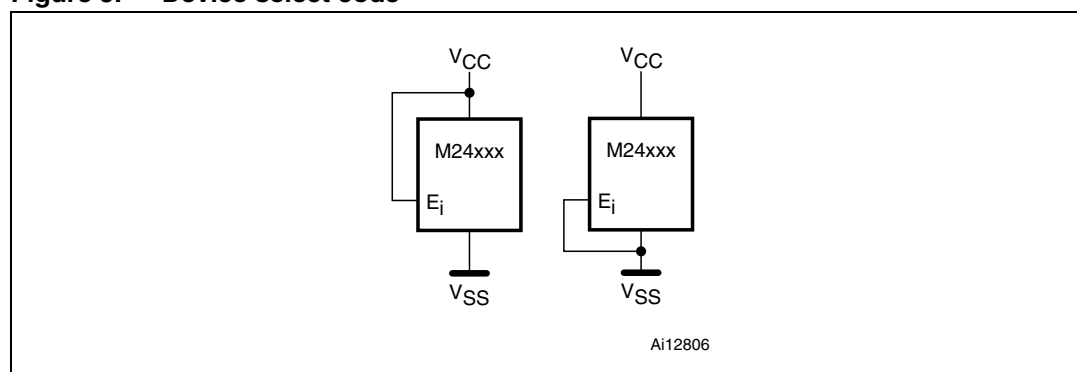
2.2 Serial Data (SDA)

SDA is an input/output used to transfer data in or data out of the device. SDA(out) is an open drain output that may be wire-OR'ed with other open drain or open collector signals on the bus. A pull up resistor must be connected ([Figure 13](#) indicates how to calculate the value of the pull-up resistor).

2.3 Chip Enable (E1, E2)

These input signals are used to set the value that is to be looked for on the two bits (b3, b2) of the 7-bit device select code. These inputs must be tied to V_{CC} or V_{SS} , to establish the device select code as shown in [Figure 5](#). When not connected (left floating), these inputs are read as low (0,0).

Figure 5. Device select code



2.4 Write Control (\overline{WC})

This input signal is useful for protecting the entire contents of the memory from inadvertent write operations. Write operations are disabled to the entire memory array when Write Control (\overline{WC}) is driven high. Write operations are enabled when Write Control (\overline{WC}) is either driven low or left floating.

When Write Control (\overline{WC}) is driven high, device select and address bytes are acknowledged, Data bytes are not acknowledged.

2.5 V_{SS} (ground)

V_{SS} is the reference for the V_{CC} supply voltage.

2.6 Supply voltage (V_{CC})

2.6.1 Operating supply voltage V_{CC}

Prior to selecting the memory and issuing instructions to it, a valid and stable V_{CC} voltage within the specified [$V_{CC}(\min)$, $V_{CC}(\max)$] range must be applied (see Operating conditions in [Section 8: DC and AC parameters](#)). In order to secure a stable DC supply voltage, it is recommended to decouple the V_{CC} line with a suitable capacitor (usually of the order of 10 nF to 100 nF) close to the V_{CC}/V_{SS} package pins.

This voltage must remain stable and valid until the end of the transmission of the instruction and, for a write instruction, until the completion of the internal write cycle (t_W).

2.6.2 Power-up conditions

The V_{CC} voltage has to rise continuously from 0 V up to the minimum V_{CC} operating voltage (see Operating conditions in [Section 8: DC and AC parameters](#)) and the rise time must not vary faster than 1 V/ μ s.

2.6.3 Device reset

In order to prevent inadvertent write operations during power-up, a power-on-reset (POR) circuit is included.

At power-up, the device does not respond to any instruction until V_{CC} has reached the internal reset threshold voltage. This threshold is lower than the minimum V_{CC} operating voltage (see Operating conditions in [Section 8: DC and AC parameters](#)). When V_{CC} passes over the POR threshold, the device is reset and enters the Standby Power mode; however, the device must not be accessed until V_{CC} reaches a valid and stable DC voltage within the specified [$V_{CC}(\min)$, $V_{CC}(\max)$] range (see Operating conditions in [Section 8: DC and AC parameters](#)).

In a similar way, during power-down (continuous decrease in V_{CC}), the device must not be accessed when V_{CC} drops below $V_{CC}(\min)$. When V_{CC} drops below the internal reset threshold voltage, the device stops responding to any instruction sent to it.

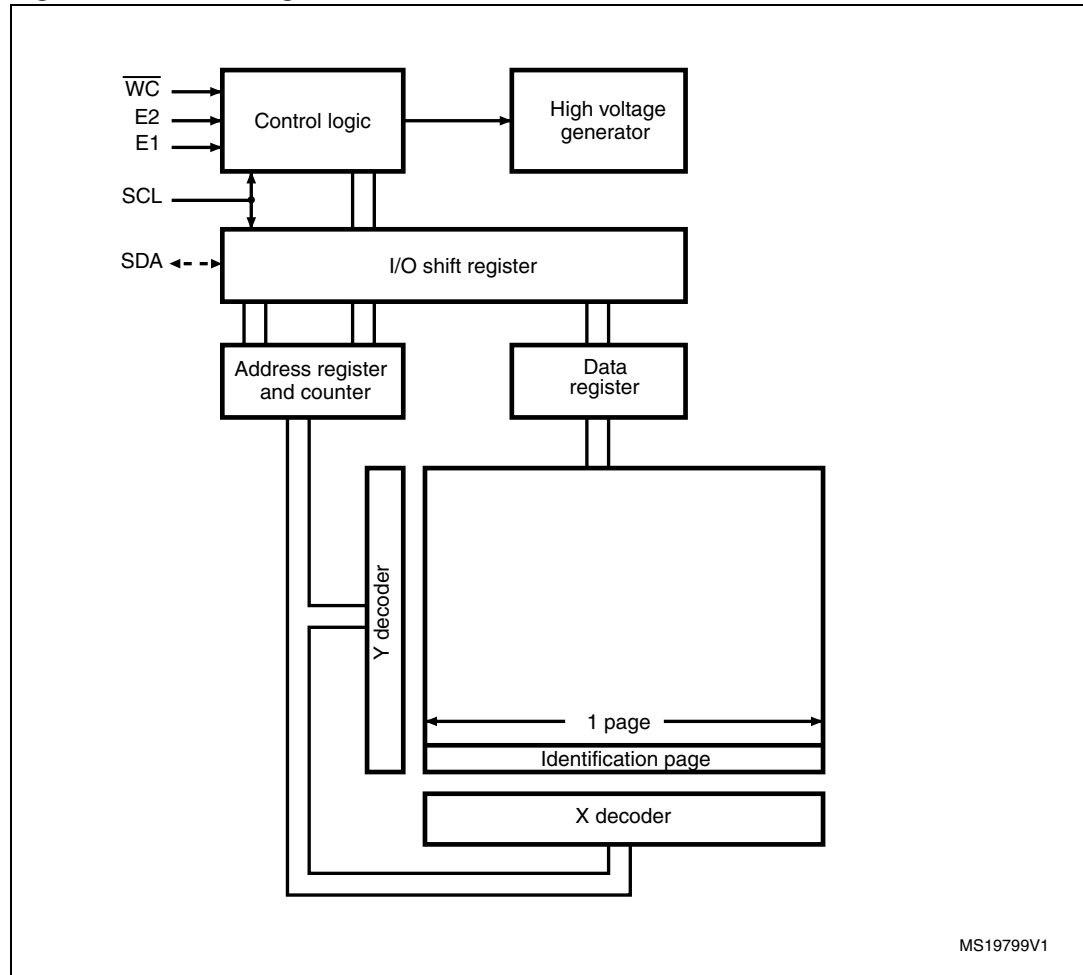
2.6.4 Power-down conditions

During power-down (continuous decrease in V_{CC}), the device must be in the Standby Power mode (mode reached after decoding a Stop condition, assuming that there is no internal write cycle in progress).

3 Memory organization

The memory is organized as shown in [Figure 6](#).

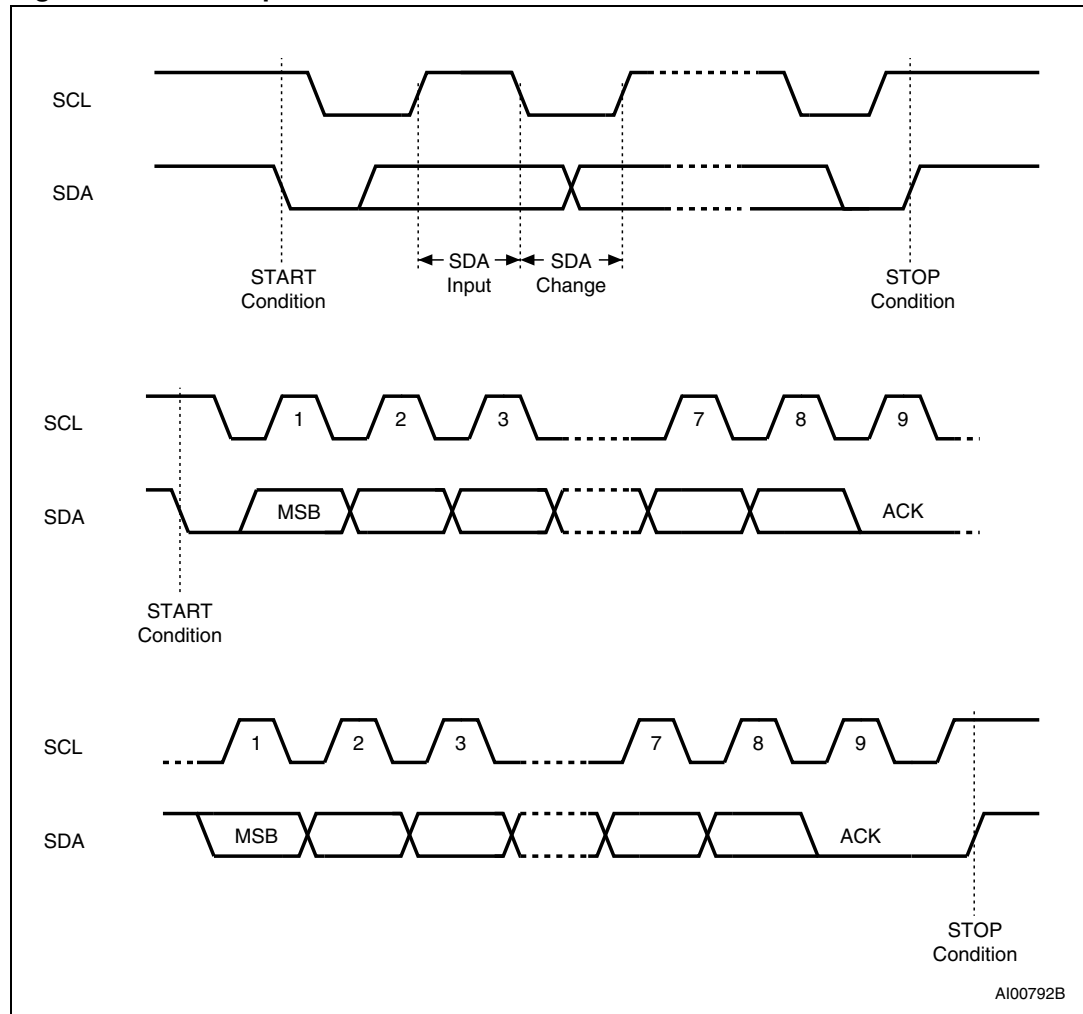
Figure 6. Block diagram



4 Device operation

The device supports the I²C protocol. This is summarized in [Figure 7](#). Any device that sends data on to the bus is defined to be a transmitter, and any device that reads the data to be a receiver. The device that controls the data transfer is known as the bus master, and the other as the slave device. A data transfer can only be initiated by the bus master, which will also provide the serial clock for synchronization. The device is always a slave in all communications.

Figure 7. I²C bus protocol



4.1 Start condition

Start is identified by a falling edge of Serial Data (SDA) while Serial Clock (SCL) is stable in the high state. A Start condition must precede any data transfer instruction. The device continuously monitors (except during a Write cycle) Serial Data (SDA) and Serial Clock (SCL) for a Start condition.

4.2 Stop condition

Stop is identified by a rising edge of Serial Data (SDA) while Serial Clock (SCL) is stable and driven high. A Stop condition terminates communication between the device and the bus master. A Read instruction that is followed by NoAck can be followed by a Stop condition to force the device into the Standby mode.

A Stop condition at the end of a Write instruction triggers the internal Write cycle.

4.3 Data input

During data input, the device samples Serial Data (SDA) on the rising edge of Serial Clock (SCL). For correct device operation, Serial Data (SDA) must be stable during the rising edge of Serial Clock (SCL), and the Serial Data (SDA) signal must change *only* when Serial Clock (SCL) is driven low.

4.4 Acknowledge bit (ACK)

The acknowledge bit is used to indicate a successful byte transfer. The bus transmitter, whether it be bus master or slave device, releases Serial Data (SDA) after sending eight bits of data. During the 9th clock pulse period, the receiver pulls Serial Data (SDA) low to acknowledge the receipt of the eight data bits.

4.5 Device addressing

To start communication between the bus master and the slave device, the bus master must initiate a Start condition. Following this, the bus master sends the device select code, shown in [Table 7](#) (on Serial Data (SDA), most significant bit first).

Table 2. Device select code

	Device type identifier ⁽¹⁾				Chip Enable address ⁽²⁾	Address bits		R \overline{W}
When accessing the memory	b7	b6	b5	b4	b3	b2	b1	b0
	1	0	1	0	E2	E1	A16	R \overline{W}
When accessing the Identification page	1	0	1	1	E2	E1	A16	R \overline{W}

1. The most significant bit, b7, is sent first.

2. E2,E1 are compared against the external pin on the memory device.

When the device select code is received, the device only responds if the Chip Enable address is the same as the value on its Chip Enable E2,E1 inputs.

The 8th bit is the Read/Write bit (\overline{RW}). This bit is set to 1 for Read and 0 for Write operations.

If a match occurs on the device select code, the corresponding device gives an acknowledgment on Serial Data (SDA) during the 9th bit time. If the device does not match the device select code, the device deselects itself from the bus, and goes into Standby mode.

5 Instructions

5.1 Write operations

Following a Start condition the bus master sends a device select code with the R/\overline{W} bit ($R\overline{W}$) reset to 0. The device acknowledges this, as shown in [Figure 8](#), and waits for two address bytes. The device responds to each address byte with an acknowledge bit, and then waits for the data byte.

Table 3. Most significant address byte

A15	A14	A13	A12	A11	A10	A9	A8
-----	-----	-----	-----	-----	-----	----	----

Table 4. Least significant address byte

A7	A6	A5	A4	A3	A2	A1	A0
----	----	----	----	----	----	----	----

The 128 Kbytes (1 Mb) are addressed with 17 address bits, the 16 lower address bits being defined by the two address bytes and the most significant address bit (A16) being included in the Device Select code (see [Table 2](#)).

When the bus master generates a Stop condition immediately after a data byte Ack bit (in the “10th bit” time slot), either at the end of a Byte Write or a Page Write, the internal Write cycle t_W is triggered. A Stop condition at any other time slot does not trigger the internal Write cycle.

After the Stop condition and the successful completion of an internal Write cycle (t_W), the device internal address counter is automatically incremented to point to the next byte after the last modified byte.

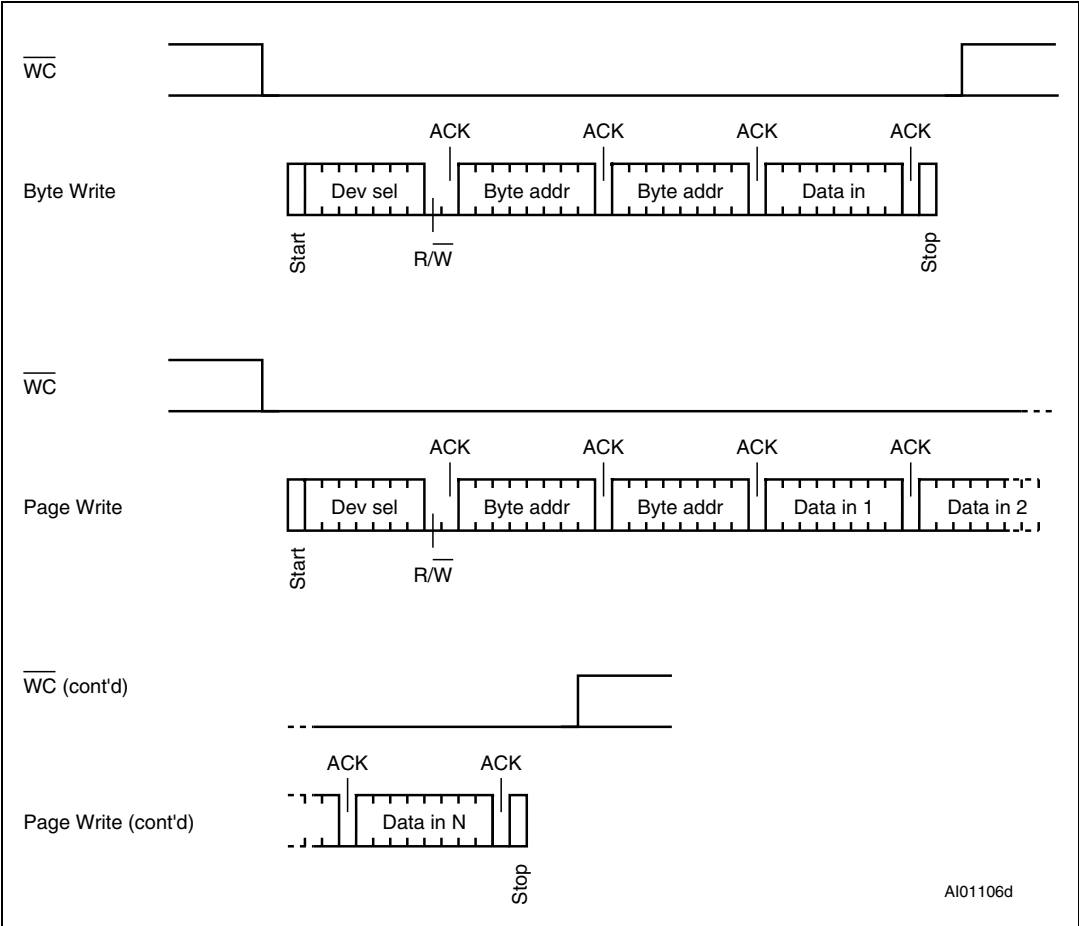
During the internal Write cycle, Serial Data (SDA) is disabled internally, and the device does not respond to any requests.

If the Write Control input (WC) is driven High, the Write instruction is not executed and the accompanying data bytes are *not* acknowledged, as shown in [Figure 9](#).

5.1.1 Byte Write

After the device select code and the address bytes, the bus master sends one data byte. If the addressed location is Write-protected, by Write Control (\overline{WC}) being driven high, the device replies with NoAck, and the location is not modified. If, instead, the addressed location is not Write-protected, the device replies with Ack. The bus master terminates the transfer by generating a Stop condition, as shown in [Figure 8](#).

Figure 8. Write mode sequences with $\overline{WC} = 0$ (data write enabled)



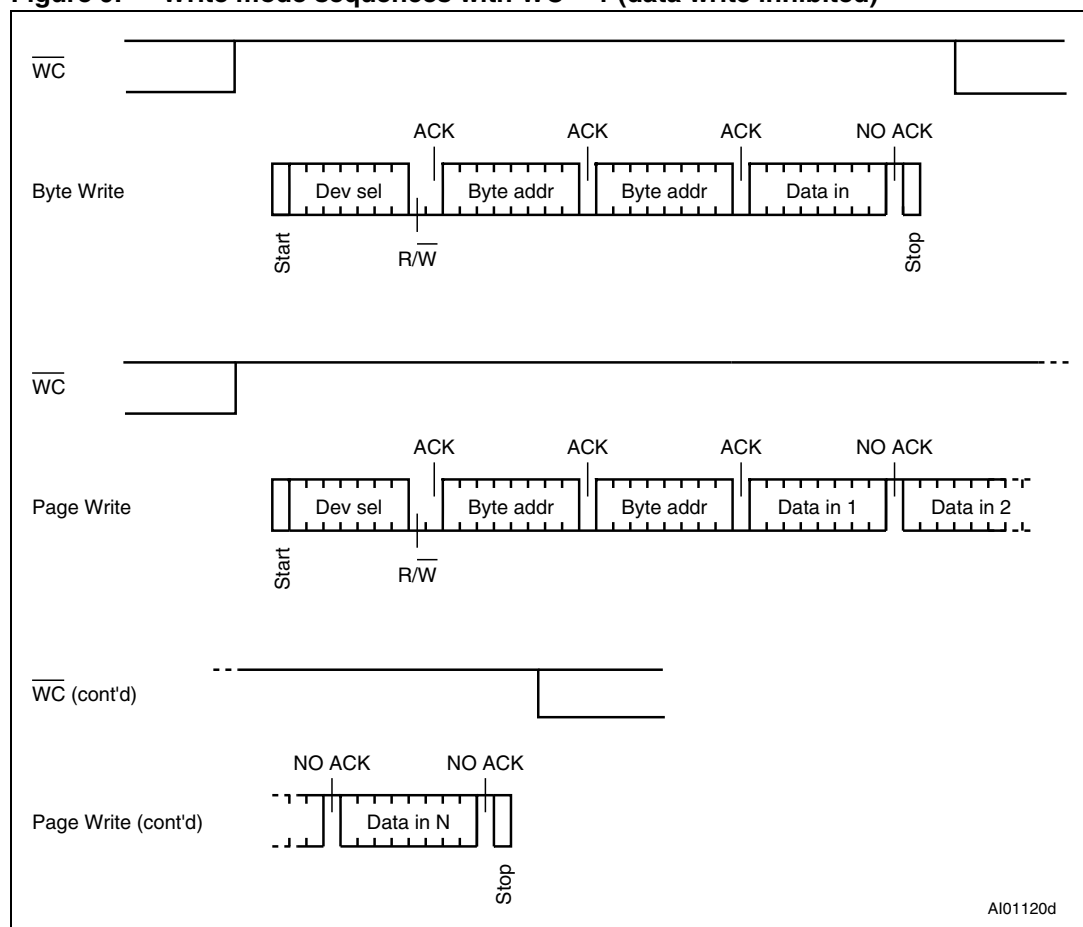
5.1.2 Page Write

The Page Write mode allows up to 256 bytes to be written in a single Write cycle, provided that they are all located in the same page in the memory: that is, the most significant memory address bits, b16-b8, are the same. If more bytes are sent than will fit up to the end of the page, a condition known as “roll-over” occurs. In case of roll-over, the first bytes of the page are overwritten.

The bus master sends from 1 to 256 bytes of data, each of which is acknowledged by the device if Write Control (\overline{WC}) is low. If Write Control (\overline{WC}) is high, the contents of the addressed memory location are not modified, and each data byte is followed by a NoAck, as shown in [Figure 9](#). After each transferred byte, the internal page address counter is incremented.

The transfer is terminated by the bus master generating a Stop condition.

Figure 9. Write mode sequences with $\overline{WC} = 1$ (data write inhibited)



5.1.3 Write Identification Page (M24M01-D only)

The Identification Page (256 bytes) is an additional page which can be written and (later) permanently locked in Read-only mode. It is written by issuing the Write Identification Page instruction. This instruction uses the same protocol and format as Page Write (into memory array), except for the following differences:

- Device type identifier = 1011b
- MSB address bits A16/A8 are don't care except for address bit A10 which must be '0'.
LSB address bits A7/A0 define the byte address inside the Identification page.

If the Identification page is locked, the data bytes transferred during the Write Identification Page instruction are not acknowledged (NoAck).

5.1.4 Lock Identification Page (M24M01-D only)

The Lock Identification Page instruction (Lock ID) permanently locks the Identification page in Read-only mode. The Lock ID instruction is similar to Byte Write (into memory array) with the following specific conditions:

- Device type identifier = 1011b
- Address bit A10 must be '1'; all other address bits are don't care
- The data byte must be equal to the binary value xxxx xx1x, where x is don't care

5.1.5 ECC (Error Correction Code) and Write cycling

The Error Correction Code (ECC) is an internal logic function which is transparent for the I²C communication protocol.

The ECC logic is implemented on each group of four EEPROM bytes^(a). Inside a group, if a single bit out of the four bytes happens to be erroneous during a Read operation, the ECC detects this bit and replaces it with the correct value. The read reliability is therefore much improved.

Even if the ECC function is performed on groups of four bytes, a single byte can be written/cycled independently. In this case, the ECC function also writes/cycles the three other bytes located in the same group^(a). As a consequence, the maximum cycling budget is defined at group level and the cycling can be distributed over the 4 bytes of the group: the sum of the cycles seen by byte0, byte1, byte2 and byte3 of the same group must remain below the maximum value defined in [Table 9: Cycling performance by groups of four bytes](#).

a. A group of four bytes is located at addresses $[4*N, 4*N+1, 4*N+2, 4*N+3]$, where N is an integer.

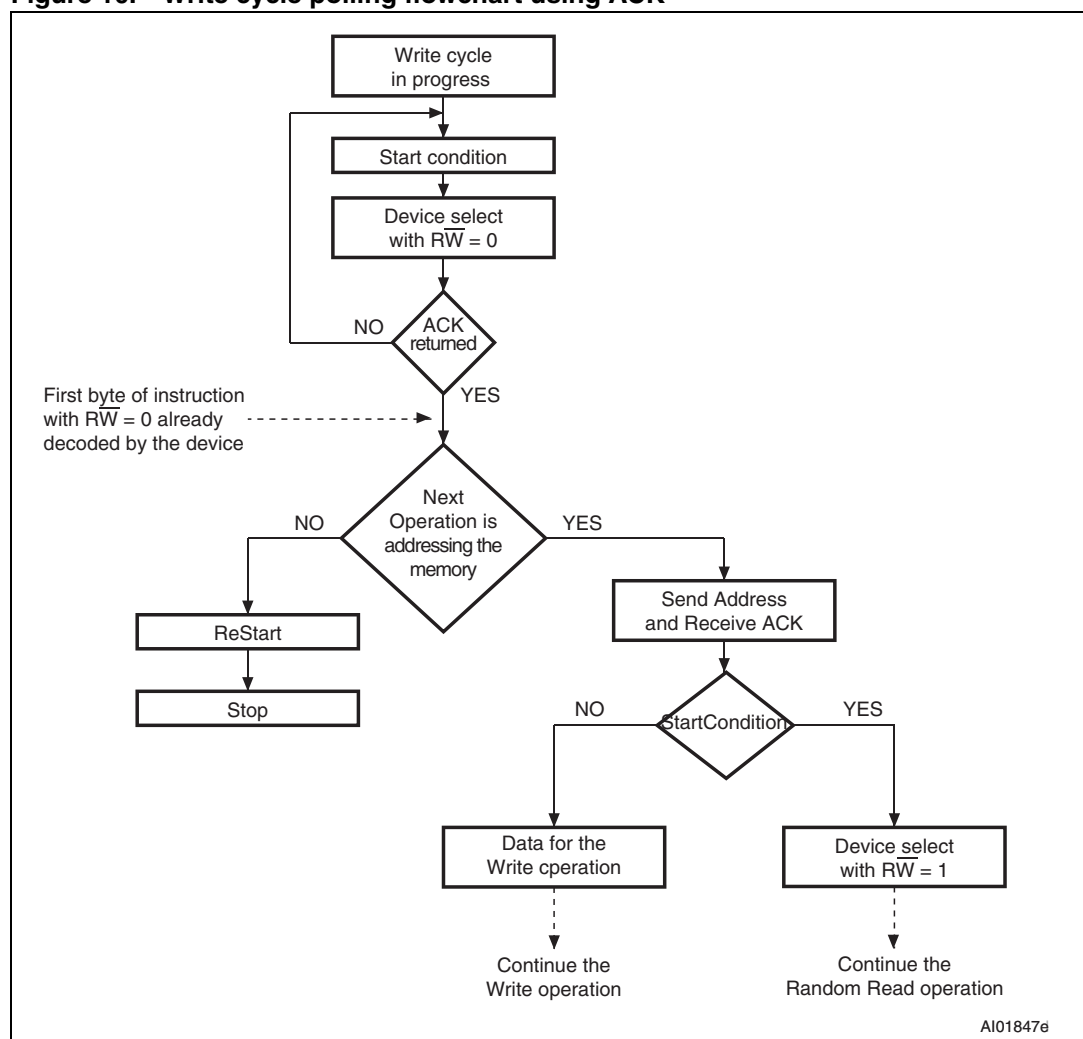
5.1.6 Minimizing Write delays by polling on ACK

The maximum Write time (t_w) is shown in AC characteristics tables in [Section 8: DC and AC parameters](#), but the typical time is shorter. To make use of this, a polling sequence can be used by the bus master.

The sequence, as shown in [Figure 10](#), is:

- Initial condition: a Write cycle is in progress.
- Step 1: the bus master issues a Start condition followed by a device select code (the first byte of the new instruction).
- Step 2: if the device is busy with the internal Write cycle, no Ack will be returned and the bus master goes back to Step 1. If the device has terminated the internal Write cycle, it responds with an Ack, indicating that the device is ready to receive the second part of the instruction (the first byte of this instruction having been sent during Step 1).

Figure 10. Write cycle polling flowchart using ACK

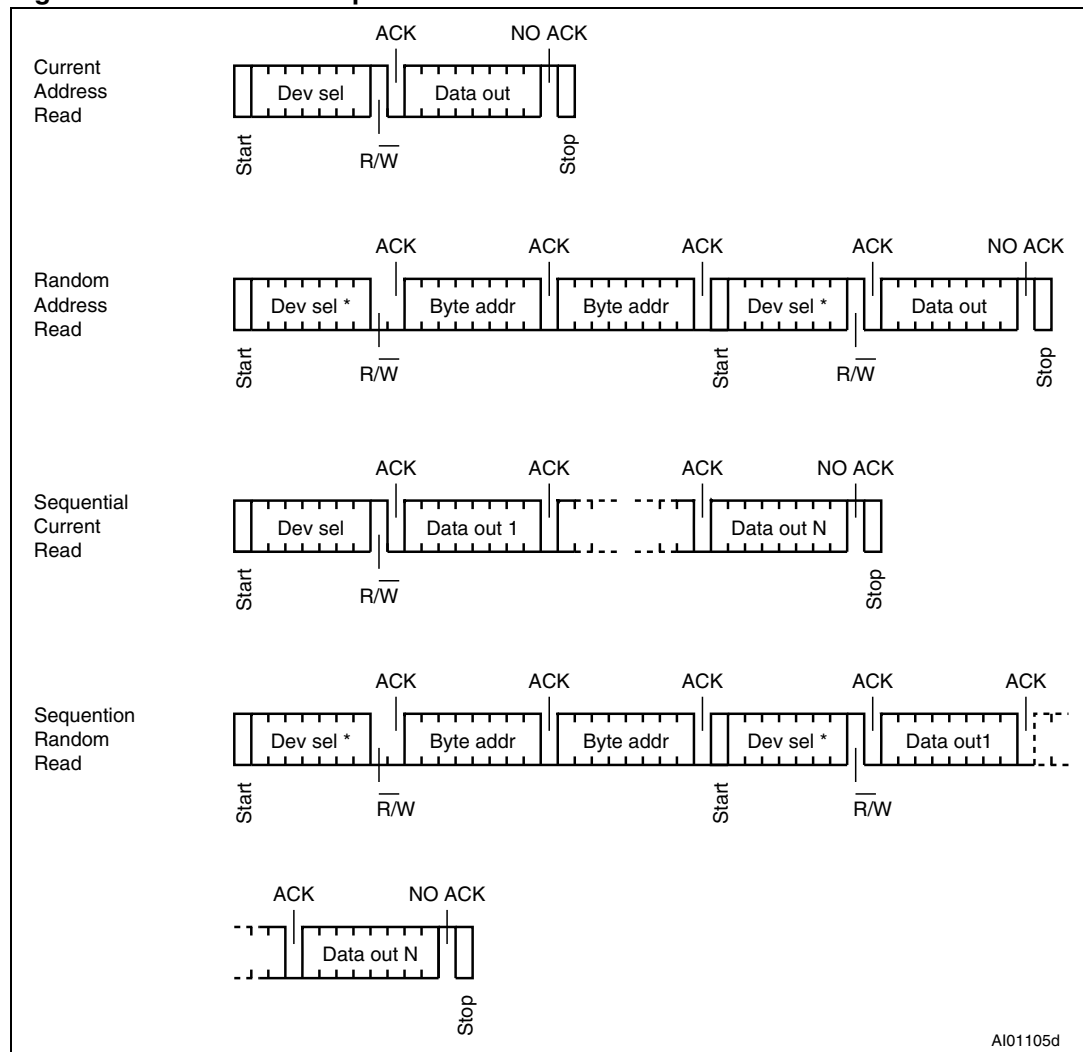


1. The seven most significant bits of the Device Select code of a Random Read (bottom right box in the figure) must be identical to the seven most significant bits of the Device Select code of the Write (polling instruction in the figure).

5.2 Read operations

Read operations are performed independently of the state of the Write Control (\overline{WC}) signal. After the successful completion of a Read operation, the device's internal address counter is incremented by one, to point to the next byte address.

Figure 11. Read mode sequences



5.2.1 Random Address Read

A dummy Write is first performed to load the address into this address counter (as shown in [Figure 11](#)) but *without* sending a Stop condition. Then, the bus master sends another Start condition, and repeats the device select code, with the R/W bit set to 1. The device acknowledges this, and outputs the contents of the addressed byte. The bus master must *not* acknowledge the byte, and terminates the transfer with a Stop condition.

5.2.2 Current Address Read

For the Current Address Read operation, following a Start condition, the bus master only sends a device select code with the R/\overline{W} bit set to 1. The device acknowledges this, and outputs the byte addressed by the internal address counter. The counter is then incremented. The bus master terminates the transfer with a Stop condition, as shown in [Figure 11](#), without acknowledging the byte.

5.2.3 Sequential Read

This operation can be used after a Current Address Read or a Random Address Read. The bus master *does* acknowledge the data byte output, and sends additional clock pulses so that the device continues to output the next byte in sequence. To terminate the stream of bytes, the bus master must *not* acknowledge the last byte, and *must* generate a Stop condition, as shown in [Figure 11](#).

The output data comes from consecutive addresses, with the internal address counter automatically incremented after each byte output. After the last memory address, the address counter 'rolls-over', and the device continues to output data from memory address 00h.

5.3 Read Identification Page (M24M01-D only)

The Identification Page (256 bytes) is an additional page which can be written and (later) permanently locked in Read-only mode.

The Identification Page can be read by issuing an Read Identification Page instruction. This instruction uses the same protocol and format as the Random Address Read (from memory array) with device type identifier defined as 1011b. The MSB address bits A16/A8 are don't care, the LSB address bits A7/A0 define the byte address inside the Identification Page. The number of bytes to read in the ID page must not exceed the page boundary (e.g.: when reading the Identification Page from location 100d, the number of bytes should be less than or equal to 156, as the ID page boundary is 256 bytes).

5.4 Read the lock status (M24M01-D only)

The locked/unlocked status of the Identification page can be checked by transmitting a specific truncated command [Identification Page Write instruction + one data byte] to the device. The device returns an acknowledge bit if the Identification page is unlocked, otherwise a NoAck bit if the Identification page is locked.

Right after this, it is recommended to transmit to the device a Start condition followed by a Stop condition, so that:

- Start: the truncated command is not executed because the Start condition resets the device internal logic,
- Stop: the device is then set back into Standby mode by the Stop condition.

5.4.1 Acknowledge in Read mode

For all Read instructions, the device waits, after each byte read, for an acknowledgment during the 9th bit time. If the bus master does not drive Serial Data (SDA) low during this time, the device terminates the data transfer and switches to its Standby mode.

6 Initial delivery state

The device is delivered with all bits set to 1 (both in the memory array and in the Identification page - that is, each byte contains FFh).

7 Maximum rating

Stressing the device outside the ratings listed in [Table 5](#) may cause permanent damage to the device. These are stress ratings only, and operation of the device at these, or any other conditions outside those indicated in the operating sections of this specification, is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 5. Absolute maximum ratings

Symbol	Parameter	Min.	Max.	Unit
	Ambient operating temperature	−40	130	°C
T _{STG}	Storage temperature	−65	150	°C
T _{LEAD}	Lead temperature during soldering	see note ⁽¹⁾		°C
V _{IO}	Input or output range	−0.50	V _{CC} +0.6	V
I _{OL}	DC output current (SDA = 0)	-	5	mA
V _{CC}	Supply voltage	−0.50	6.5	V
V _{ESD}	Electrostatic pulse (Human Body model) ⁽²⁾	-	4000 ⁽³⁾	V

1. Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (RoHS) 2002/95/EU.
2. Positive and negative pulses applied on pin pairs, according to AEC-Q100-002 (compliant with JEDEC Std JESD22-A114, C1=100 pF, R1=1500 Ω, R2=500 Ω).
3. 3000 V for previous devices (process letter A or B).

8 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device.

Table 6. Operating conditions (voltage range R)

Symbol	Parameter	Min.	Max.	Unit
V_{CC}	Supply voltage	1.8	5.5	V
T_A	Ambient operating temperature	-40	85	°C
f_C	Operating clock frequency	-	1	MHz

Table 7. Operating conditions (voltage range F)

Symbol	Parameter	Min.	Max.	Unit
V_{CC}	Supply voltage	1.7	5.5	V
T_A	Ambient operating temperature	-40	85	°C
f_C	Operating clock frequency	-	1	MHz

Table 8. AC measurement conditions

Symbol	Parameter	Min.	Max.	Unit
C_{bus}	Load capacitance	100		pF
	SCL input rise/fall time, SDA input fall time		50	ns
	Input levels	0.2 V_{CC} to 0.8 V_{CC}		V
	Input and output timing reference levels	0.3 V_{CC} to 0.7 V_{CC}		V

Figure 12. AC measurement I/O waveform

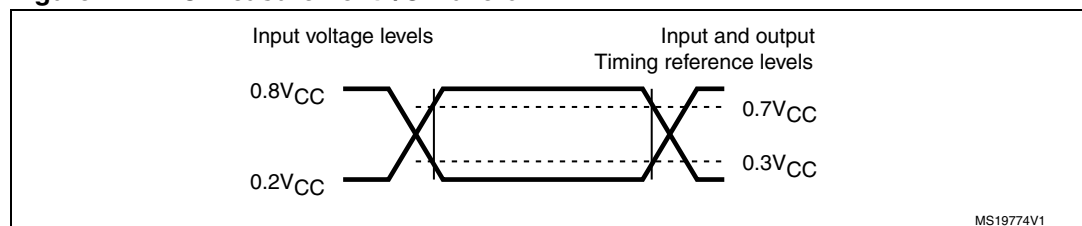


Table 9. Cycling performance by groups of four bytes

Symbol	Parameter	Test condition ⁽¹⁾	Max.	Unit
Ncycle	Write cycle endurance ⁽²⁾	$TA \leq 25\text{ }^{\circ}\text{C}, 1.8\text{ V} < V_{CC} < 5.5\text{ V}$	4,000,000	Write cycle ⁽³⁾
		$TA = 85\text{ }^{\circ}\text{C}, 1.8\text{ V} < V_{CC} < 5.5\text{ V}$	1,200,000	

1. Cycling performance for products identified by process letter K.
2. The Write cycle endurance is defined for groups of four data bytes located at addresses $[4*N, 4*N+1, 4*N+2, 4*N+3]$ where N is an integer. The Write cycle endurance is defined by characterization and qualification.
3. A Write cycle is executed when either a Page Write, a Byte Write, a Write Identification Page or a Lock Identification Page instruction is decoded. When using the Byte Write, the Page Write or the Write Identification Page, refer also to [Section 5.1.5: ECC \(Error Correction Code\) and Write cycling](#).

Table 10. Memory cell data retention

Parameter	Test condition	Min.	Unit
Data retention ⁽¹⁾	$TA = 55\text{ }^{\circ}\text{C}$	200	Year

1. For products identified by process letter K. The data retention is not tested in production but defined from characterization and qualification results.

Table 11. Input parameters

Symbol	Parameter ⁽¹⁾	Test condition	Min.	Max.	Unit
C_{IN}	Input capacitance (SDA)			8	pF
C_{IN}	Input capacitance (other pins)			6	pF
Z_L	Input impedance (\overline{WC})	$V_{IN} < 0.3 V_{CC}$	30		k Ω
Z_H		$V_{IN} > 0.7 V_{CC}$	400		k Ω

1. Sampled only, not 100% tested.

Table 12. DC characteristics (voltage range R, device grade 6)

Symbol	Parameter	Test conditions (in addition to those in Table 6)	Min.	Max.	Unit
I_{LI}	Input leakage current (E1, E2, SCL, SDA)	$V_{IN} = V_{SS}$ or V_{CC} device in Standby mode		± 2	μA
I_{LO}	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: V_{SS} or V_{CC}		± 2	μA
I_{CC}	Supply current (Read)	$V_{CC} = 1.8 V$, $f_c = 400 kHz$		1 ⁽¹⁾	mA
		$V_{CC} = 2.5 V$, $f_c = 400 kHz$		1	mA
		$V_{CC} = 5.5 V$, $f_c = 400 kHz$		1.5 ⁽²⁾	mA
		$f_c = 1 MHz$		1.5 ⁽³⁾	mA
I_{CC0}	Supply current (Write)	During t_W		2 ⁽⁴⁾⁽⁵⁾	mA
I_{CC1}	Standby supply current	Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 1.8 V$		3 ⁽⁶⁾	μA
		Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 2.5 V$		3 ⁽⁷⁾	μA
		Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 5.5 V$		5 ⁽⁸⁾	μA
V_{IL}	Input low voltage (SCL, SDA, WC)	$1.8 V \leq V_{CC} < 2.5 V$	-0.45	$0.25 V_{CC}$	V
		$2.5 V \leq V_{CC} < 5.5 V$	-0.45	$0.30 V_{CC}$	V
V_{IH}	Input high voltage (SCL, SDA)	$1.8 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	$V_{CC}+1$	v
		$2.5 V \leq V_{CC} < 5.5 V$	$0.70 V_{CC}$	$0 V_{CC}+1$	v
V_{OL}	Output low voltage	$I_{OL} = 1.0 mA$, $V_{CC} = 1.8 V$		0.2	V
		$I_{OL} = 2.1 mA$, $V_{CC} = 2.5 V$		0.4	V
		$I_{OL} = 3.0 mA$, $V_{CC} = 5.5 V$		0.4	V

1. Devices identified by process letter A or B offer $I_{CC} = 0.8 mA$
2. The previous product identified by process letter A or B was specified with $I_{CC(max)} = 2 mA$.
3. Devices identified by process letter A or B offer $I_{CC} = 2.5 mA$.
4. Characterized only, not tested in production.
5. The previous product identified by process letter A or B was characterized with $I_{CC0(max)} = 5 mA$.
6. Devices identified by process letter A or B offer $I_{CC1} = 1 \mu A$.
7. Devices identified by process letter A or B offer $I_{CC1} = 2 \mu A$.
8. Devices identified by process letter A or B offer $I_{CC1} = 3 \mu A$.

Table 13. DC characteristics (voltage range F, device grade 6)

Symbol	Parameter	Test conditions (in addition to those in Table 6)	Min.	Max.	Unit
I_{LI}	Input leakage current (E1, E2, SCL, SDA)	$V_{IN} = V_{SS}$ or V_{CC} device in Standby mode		± 2	μA
I_{LO}	Output leakage current	SDA in Hi-Z, external voltage applied on SDA: V_{SS} or V_{CC}		± 2	μA
I_{CC}	Supply current (Read)	$V_{CC} = 1.7 V$, $f_c = 400 kHz$		1	mA
		$V_{CC} = 2.5 V$, $f_c = 400 kHz$		1	mA
		$V_{CC} = 5.5 V$, $f_c = 400 kHz$		1.5	mA
		$f_c = 1 MHz$		1.5	mA
I_{CC0}	Supply current (Write)	During t_W		2 ⁽¹⁾	mA
I_{CC1}	Standby supply current	Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 1.7 V$		3	μA
		Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 2.5 V$		3	μA
		Device not selected, $V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 5.5 V$		5	μA
V_{IL}	Input low voltage (SCL, SDA, WC)	$1.7 V \leq V_{CC} < 2.5 V$	-0.45	$0.25 V_{CC}$	V
		$2.5 V \leq V_{CC} < 5.5 V$	-0.45	$0.30 V_{CC}$	V
V_{IH}	Input high voltage (SCL, SDA)	$1.7 V \leq V_{CC} < 2.5 V$	$0.75 V_{CC}$	$V_{CC}+1$	v
		$2.5 V \leq V_{CC} < 5.5 V$	$0.70 V_{CC}$	$0 V_{CC}+1$	v
V_{OL}	Output low voltage	$I_{OL} = 1.0 mA$, $V_{CC} = 1.7 V$		0.2	V
		$I_{OL} = 2.1 mA$, $V_{CC} = 2.5 V$		0.4	V
		$I_{OL} = 3.0 mA$, $V_{CC} = 5.5 V$		0.4	V

1. Characterized only, not tested in production.

Table 14. 400 kHz AC characteristics

Symbol	Alt.	Parameter	Min.	Max.	Unit
f_C	f_{SCL}	Clock frequency	-	400	kHz
t_{CHCL}	t_{HIGH}	Clock pulse width high	600	-	ns
t_{CLCH}	t_{LOW}	Clock pulse width low	1300	-	ns
$t_{QL1QL2}^{(1)}$	t_F	SDA (out) fall time	20 ⁽²⁾	300	ns
t_{XH1XH2}	t_R	Input signal rise time	(3)	(3)	ns
t_{XL1XL2}	t_F	Input signal fall time	(3)	(3)	ns
t_{DXCH}	$t_{SU:DAT}$	Data in set up time	100	-	ns
t_{CLDX}	$t_{HD:DAT}$	Data in hold time	0	-	ns
$t_{CLQX}^{(4)}$	t_{DH}	Data out hold time	100 ⁽⁵⁾	-	ns
$t_{CLQV}^{(6)}$	t_{AA}	Clock low to next data valid (access time)	-	900	ns
t_{CHDL}	$t_{SU:STA}$	Start condition setup time	600	-	ns
t_{DLCL}	$t_{HD:STA}$	Start condition hold time	600	-	ns
t_{CHDH}	$t_{SU:STO}$	Stop condition set up time	600	-	ns
t_{DHDL}	t_{BUF}	Time between Stop condition and next Start condition	1300	-	ns
$t_{WLDL}^{(7)(2)}$	$t_{SU:WC}$	\overline{WC} set up time (before the Start condition)	0	-	μs
$t_{DHWL}^{(8)(2)}$	$t_{HD:WC}$	\overline{WC} hold time (after the Stop condition)	1	-	μs
t_W	t_{WR}	Internal Write cycle duration	-	5	ms
$t_{NS}^{(2)}$		Pulse width ignored (input filter on SCL and SDA) - single glitch	-	80 ⁽⁹⁾	ns

1. Characterized only, not tested in production.
2. With $C_L = 10$ pF.
3. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I²C specification that the input signal rise and fall times be more than 20 ns and less than 300 ns when $f_C < 400$ kHz.
4. To avoid spurious Start and Stop conditions, a minimum delay is placed between SCL=1 and the falling or rising edge of SDA.
5. The previous product identified by process letter A was specified with $t_{CLQX} = 200$ ns (min).
6. t_{CLQV} is the time (from the falling edge of SCL) required by the SDA bus line to reach either $0.3V_{CC}$ or $0.7V_{CC}$, assuming that $R_{bus} \times C_{bus}$ time constant is within the values specified in [Figure 13](#).
7. $\overline{WC}=0$ set up time condition to enable the execution of a WRITE command.
8. $\overline{WC}=0$ hold time condition to enable the execution of a WRITE command.
9. The previous product identified by process letter A or B was specified with $t_{NS} = 100$ ns (max).

Table 15. 1 MHz AC characteristics

Symbol	Alt.	Parameter	Min.	Max.	Unit
f_C	f_{SCL}	Clock frequency	0	1	MHz
t_{CHCL}	t_{HIGH}	Clock pulse width high	300	-	ns
t_{CLCH}	t_{LOW}	Clock pulse width low	400	-	ns
t_{XH1XH2}	t_R	Input signal rise time	(1)	(1)	ns
t_{XL1XL2}	t_F	Input signal fall time	(1)	(1)	ns
$t_{QL1QL2}^{(8)}$	t_F	SDA (out) fall time	-	120	ns
t_{DXCX}	$t_{SU:DAT}$	Data in setup time	80	-	ns
t_{CLDX}	$t_{HD:DAT}$	Data in hold time	0	-	ns
$t_{CLQX}^{(2)}$	t_{DH}	Data out hold time	50	-	ns
$t_{CLQV}^{(3)}$	t_{AA}	Clock low to next data valid (access time)	-	500	ns
t_{CHDL}	$t_{SU:STA}$	Start condition setup time	250	-	ns
t_{DLCL}	$t_{HD:STA}$	Start condition hold time	250	-	ns
t_{CHDH}	$t_{SU:STO}$	Stop condition setup time	250	-	ns
t_{DHDL}	t_{BUF}	Time between Stop condition and next Start condition	500	-	ns
$t_{WLDL}^{(4)(8)}$	$t_{SU:WC}$	\overline{WC} set up time (before the Start condition)	0	-	μs
$t_{DHWL}^{(5)(8)}$	$t_{HD:WC}$	\overline{WC} hold time (after the Stop condition)	1	-	μs
t_W	t_{WR}	Write time	-	5	ms
$t_{NS}^{(6)}$		Pulse width ignored (input filter on SCL and SDA)	-	80 ⁽⁷⁾	ns

1. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I²C specification that the input signal rise and fall times be more than 20 ns and less than 120 ns when $f_C < 1$ MHz.
2. To avoid spurious Start and Stop conditions, a minimum delay is placed between SCL=1 and the falling or rising edge of SDA.
3. t_{CLQV} is the time (from the falling edge of SCL) required by the SDA bus line to reach either 0.3 V_{CC} or 0.7 V_{CC} , assuming that the $R_{bus} \times C_{bus}$ time constant is within the values specified in [Figure 14](#).
4. $\overline{WC}=0$ set up time condition to enable the execution of a WRITE command.
5. $\overline{WC}=0$ hold time condition to enable the execution of a WRITE command.
6. Characterized only, not tested in production.
7. The previous product identified by process letter A or B was specified with $t_{NS} = 50$ ns (max).

Figure 13. Maximum R_{bus} value versus bus parasitic capacitance (C_{bus}) for an I²C bus at maximum frequency $f_C = 400$ kHz

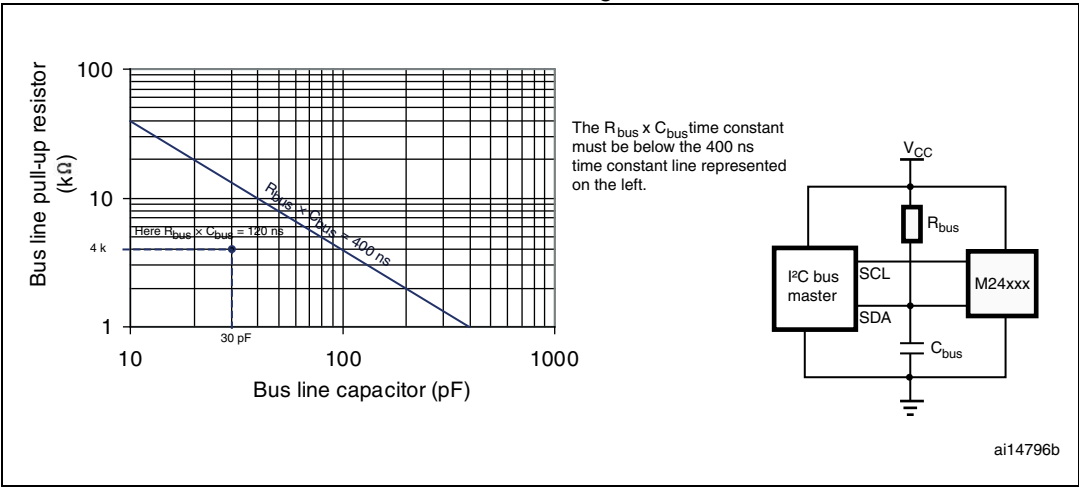


Figure 14. Maximum R_{bus} value versus bus parasitic capacitance C_{bus}) for an I²C bus at maximum frequency $f_C = 1$ MHz

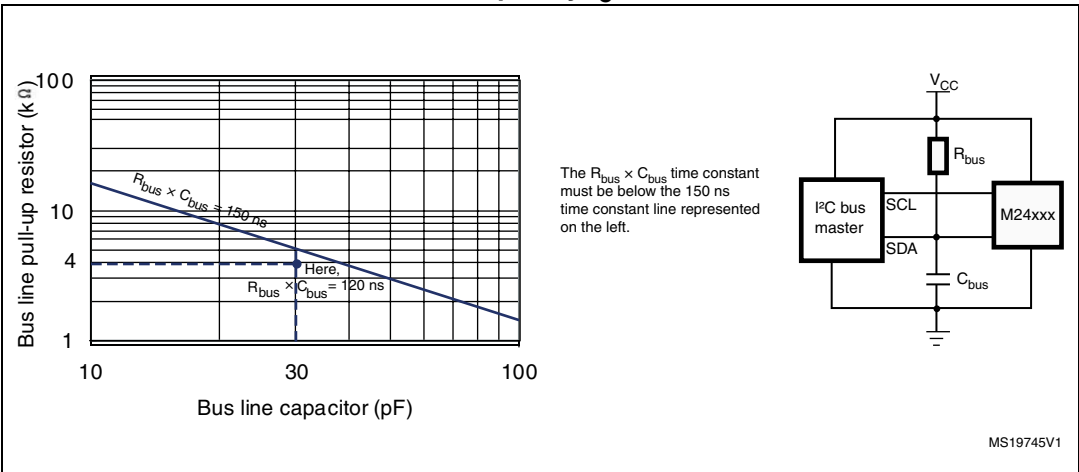
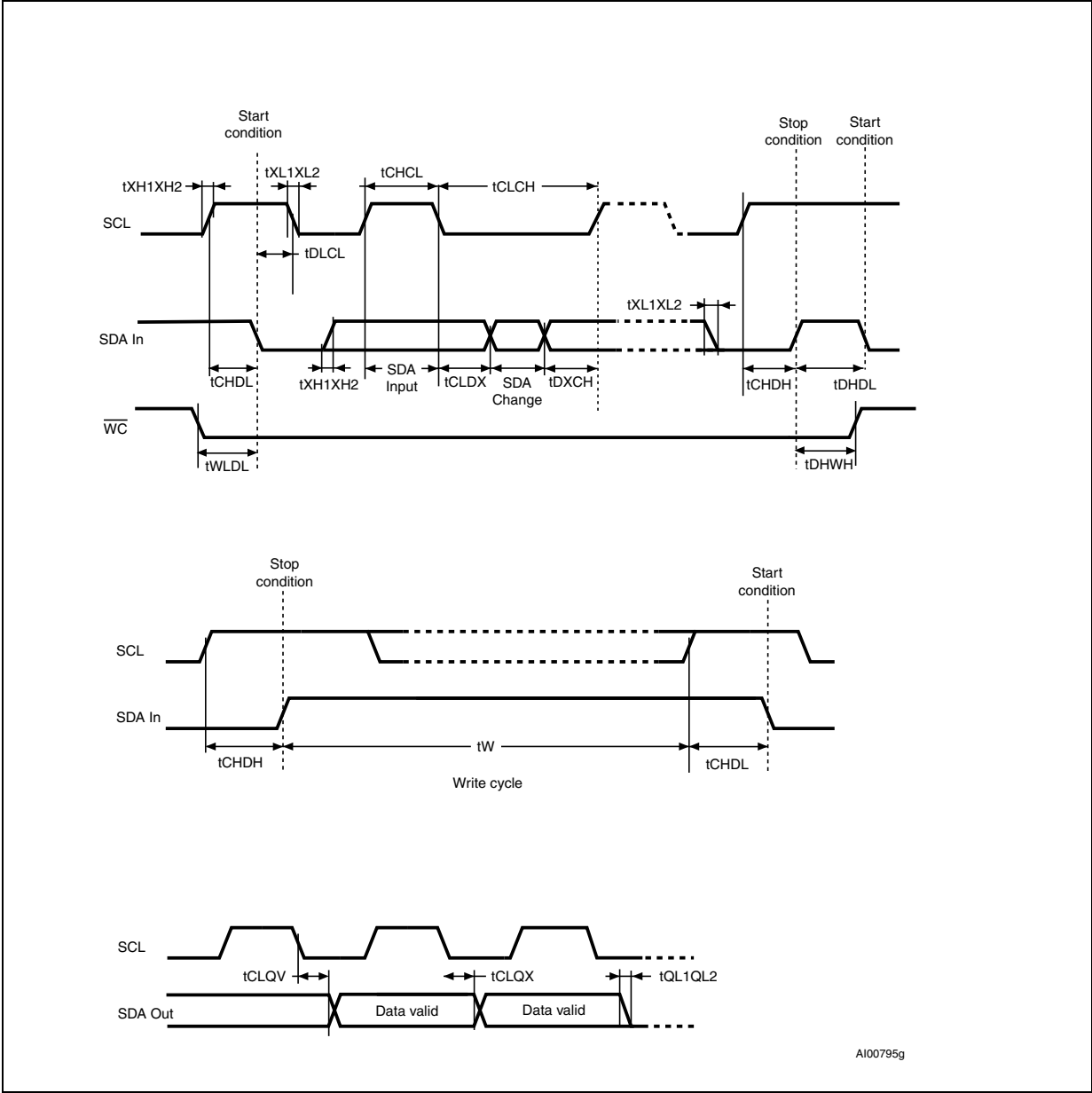


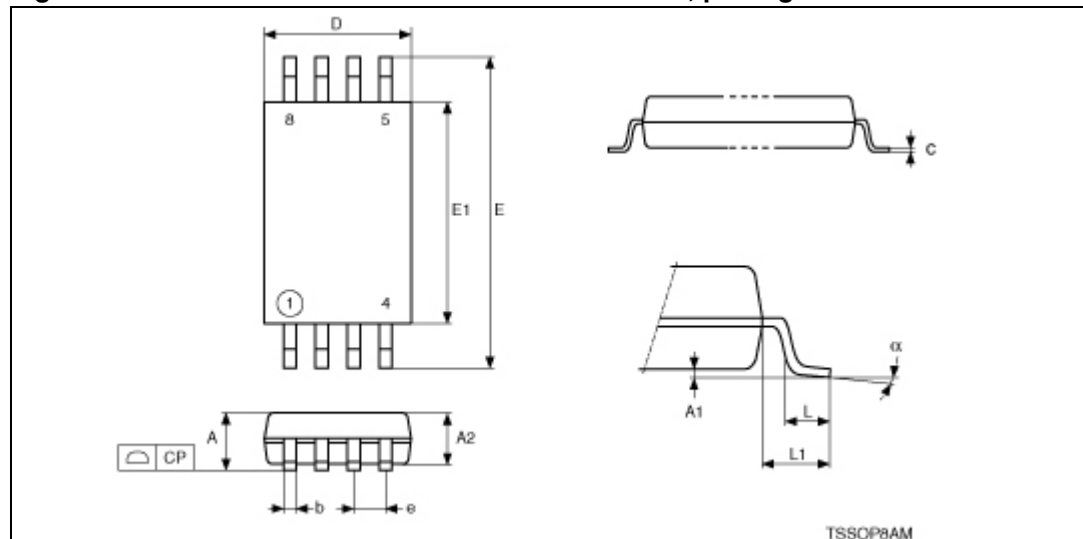
Figure 15. AC waveforms



9 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 16. TSSOP8 – 8-lead thin shrink small outline, package outline



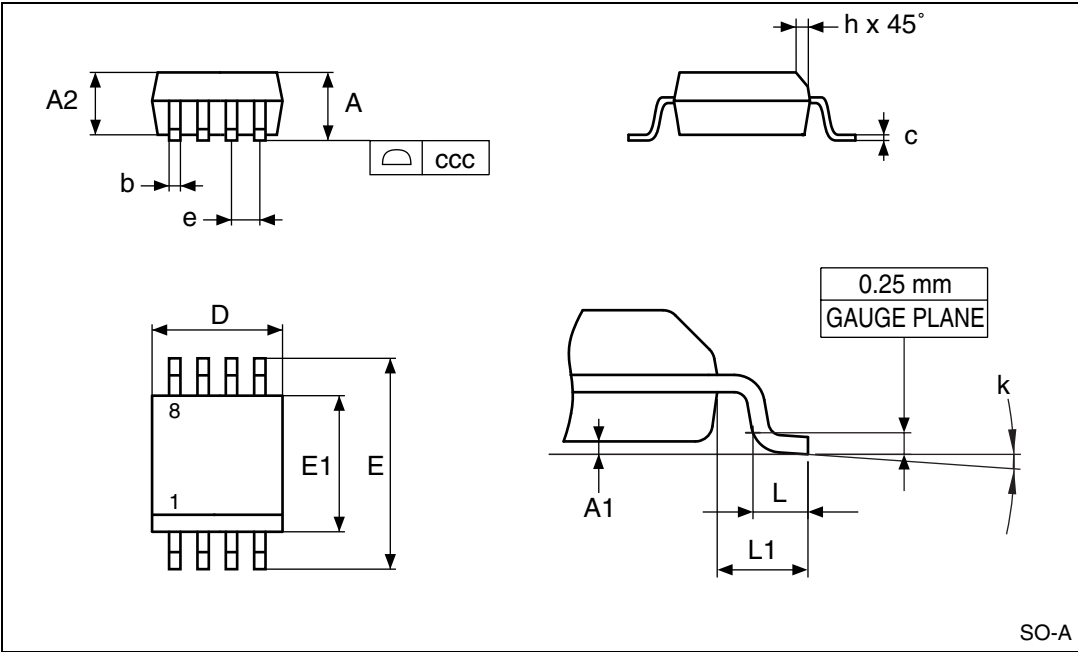
1. Drawing is not to scale.

Table 16. TSSOP8 – 8-lead thin shrink small outline, package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			1.200			0.0472
A1		0.050	0.150		0.0020	0.0059
A2	1.000	0.800	1.050	0.0394	0.0315	0.0413
b		0.190	0.300		0.0075	0.0118
c		0.090	0.200		0.0035	0.0079
CP			0.100			0.0039
D	3.000	2.900	3.100	0.1181	0.1142	0.1220
e	0.650	–	–	0.0256	–	–
E	6.400	6.200	6.600	0.2520	0.2441	0.2598
E1	4.400	4.300	4.500	0.1732	0.1693	0.1772
L	0.600	0.450	0.750	0.0236	0.0177	0.0295
L1	1.000			0.0394		
α		0°	8°		0°	8°

1. Values in inches are converted from mm and rounded to four decimal digits.

Figure 17. SO8N – 8 lead plastic small outline, 150 mils body width, package outline

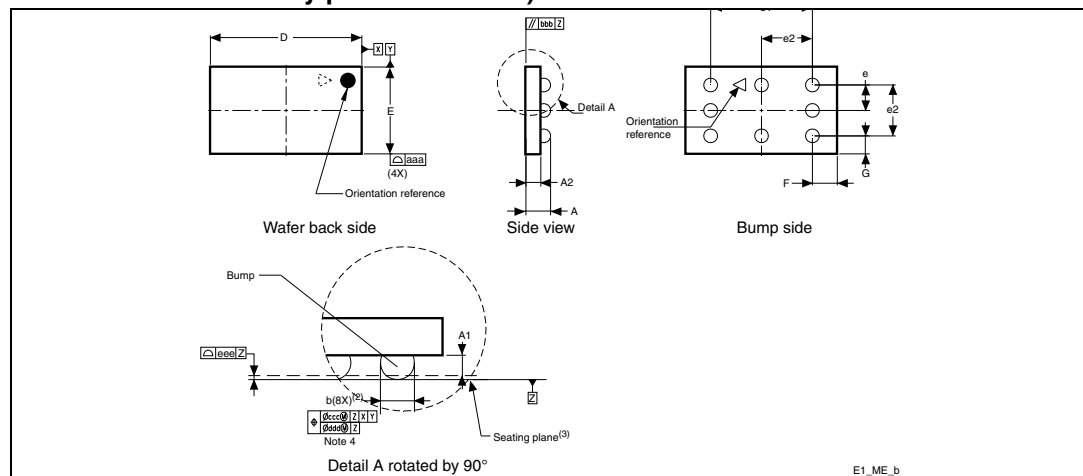


1. Drawing is not to scale.

Table 17. SO8N – 8 lead plastic small outline, 150 mils body width, package data

Symbol	millimeters			inches ⁽¹⁾		
	Typ	Min	Max	Typ	Min	Max
A			1.750			0.0689
A1		0.100	0.250		0.0039	0.0098
A2		1.250			0.0492	
b		0.280	0.480		0.0110	0.0189
c		0.170	0.230		0.0067	0.0091
ccc			0.100			0.0039
D	4.900	4.800	5.000	0.1929	0.1890	0.1969
E	6.000	5.800	6.200	0.2362	0.2283	0.2441
E1	3.900	3.800	4.000	0.1535	0.1496	0.1575
e	1.270			0.0500		
h		0.250	0.500		0.0098	0.0197
k		0°	8°		0°	8°
L		0.400	1.270		0.0157	0.0500
L1	1.040			0.0409		

1. Values in inches are converted from mm and rounded to four decimal digits.

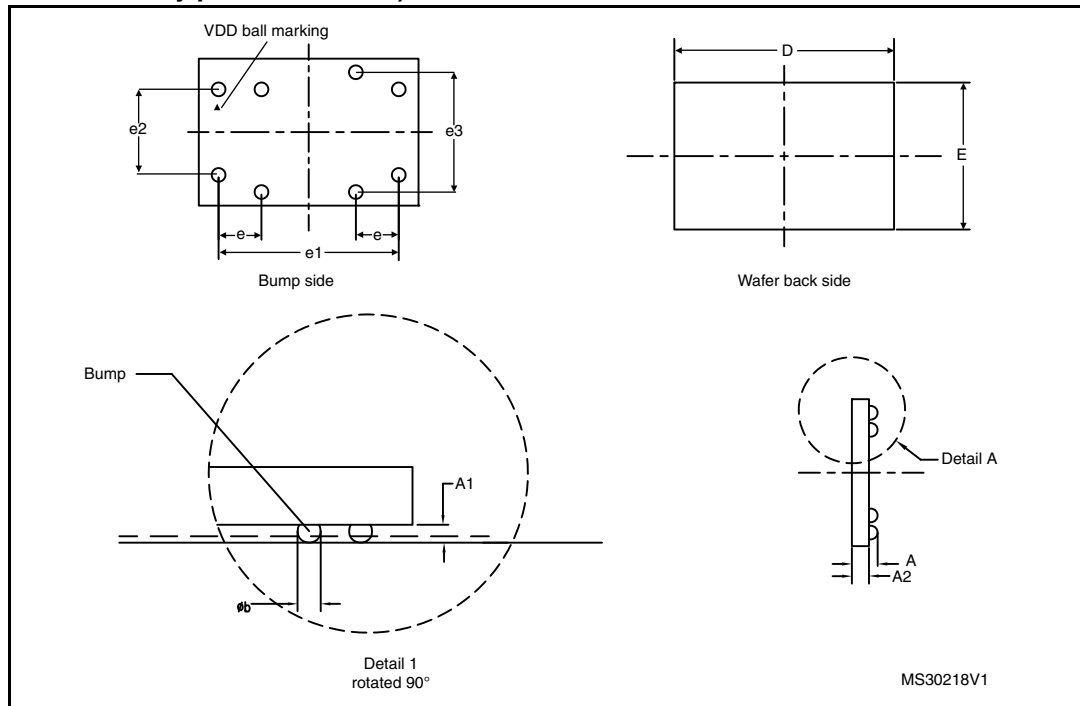
Figure 18. Standard WLCSP8 – Wafer level chip scale package outline (for die identified by process letter A)

- 1 Drawing is not to scale and corresponds to preliminary data.
- 2 The dimension is measured at the maximum bump diameter parallel to primary datum Z.
- 3 The primary datum Z and seating plane are defined by the spherical crowns of the bump.
- 4 Bump position designation per JESD 95-1, SPP-010.

Table 18. WLCSP8 – Wafer level chip scale package mechanical data⁽¹⁾

Symbol	millimeters			inches ⁽²⁾		
	Typ	Min	Max	Typ	Min	Max
A	0.580	0.555	0.605	0.0228	0.0219	0.0238
A1	0.230			0.0091		
A2	0.350			0.0138		
b	0.322			0.0127		
D	3.570		3.685	0.1406		0.1451
E	2.050		2.165	0.0807		0.0852
e	0.600			0.0236		
e1	2.400			0.0945		
e2	1.200			0.0472		
F	0.585			0.0230		
G	0.424			0.0167		
aaa	0.110			0.0043		
bbb	0.110			0.0043		
ccc	0.110			0.0043		
ddd	0.060			0.0024		
eee	0.060			0.0024		
N (number of bumps)	8					

1. Preliminary data.
2. Values in inches are converted from mm and rounded to four decimal digits.

Figure 19. Thin WLCSP – Wafer level chip size package outline (for die identified by process letter K)**Table 19. WLCSP – Wafer level chip size package mechanical data**

Symbol	millimeters			inches ⁽¹⁾		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	0.300	0.280	0.320	0.0118	0.0110	0.0126
A1	0.100			0.0039		
A2	0.200			0.0079		
b	0.126			0.0050		
D	2.560			0.1008		
E	1.698		1.823	0.0669		0.0676
e	1.000			0.0394		
e1	1.200			0.0472		
e2	1.100			0.0433		
e3	0.500			0.0197		

1. Values in inches are converted from mm and rounded to four decimal digits.

10 Part numbering

Table 20. Ordering information scheme

Example:	M24M01-D	R	MN	6	T	P	/K
Device type M24 = I ² C serial access EEPROM							
Device function M01 = 1 Mbit (128 Kb × 8 bits)							
Device family Blank: Without Identification page -D: With additional Identification page							
Operating voltage R = V _{CC} = 1.8 V to 5.5 V F = V _{CC} = 1.7 V to 5.5 V							
Package MN = SO8 (150 mil width) ⁽¹⁾ DW = TSSOP8 (169 mil width) ⁽¹⁾ CS = standard WLCSP CT = thin WLCSP							
Device grade 6 = Industrial: device tested with standard test flow over –40 to 85 °C							
Option blank = standard packing T = Tape and reel packing							
Plating technology P = ECOPACK [®] (RoHS compliant)							
Process⁽²⁾ /A, /B or /K= Manufacturing technology code							

1. RoHS-compliant and halogen-free (ECOPACK2[®])
2. The process letter applies to WLCSP devices only.

For a list of available options (speed, package, etc.) or for further information on any aspect of the devices, please contact your nearest ST sales office.

11 Revision history

Table 21. Document revision history

Date	Revision	Changes
07-Dec-2006	1	Initial release.
02-Oct-2007	2	Document status promoted from Preliminary Data to full Datasheet. Section 2.6: Supply voltage (VCC) updated. Note 1 updated to latest standard revision below Table 5: Absolute maximum ratings . V_{IL} , V_{IH} modified and, rise/fall time corrected in Test conditions in Table 11: DC characteristics (M24M01-R and M24M01-HR) . Package values in inches calculated from mm and rounded to 4 decimal digits (note added below package mechanical data tables in Section 7: Package mechanical data .
26-Nov-2007	3	1 MHz maximum clock frequency added: – Figure 6: Maximum Rbus value versus bus parasitic capacitance (Cbus) for an I2C bus at maximum frequency fC = 1MHz – Table 14: AC characteristics at 1 MHz (M24M01-HR) added. t_{NS} moved from Table 8: Input parameters to Table 13: AC characteristics at 400 kHz (M24M01-R and M24M01-W) . Note removed below Table 8 . In Table 13 , t_{CH1CH2} , t_{CL1CL2} and t_{DL1DL2} removed, t_{XH1XH2} , t_{XL1XL2} added, t_{DL1DL2} max modified, notes modified. Figure 5: Maximum Rbus value versus bus parasitic capacitance (Cbus) for an I2C bus at maximum frequency fC = 400 kHz modified. Figure 13: AC waveforms modified. Small text changes.
18-Mar-2008	4	M24M01-HR root part number added. Small text changes. Figure 6: Maximum Rbus value versus bus parasitic capacitance (Cbus) for an I2C bus at maximum frequency fC = 1MHz modified. Most significant address bits modified in Section 3.8: Page Write on page 15 . Test conditions modified for I_{LI} , I_{CC} and V_{OL} in Table 11: DC characteristics (M24M01-R and M24M01-HR) . TW and TNS values corrected in Table 13: AC characteristics at 400 kHz (M24M01-R and M24M01-W) . Cross-reference corrected in Note 5 below Table 14: AC characteristics at 1 MHz (M24M01-HR) .

Table 21. Document revision history (continued)

Date	Revision	Changes
02-Sep-2008	5	<p>Added: M24M01-W part number in device grade 3 temperature range (see Table 8: Operating conditions (M24M01-W), Table 12: DC characteristics (M24M01-W) and Table 17: Ordering information scheme (M24M01-x products sold in packages)).</p> <p>M24M01-R offered as a bare die (see Section 8: Part numbering and Table 18: Ordering information scheme (M24M01-R sold as bare dice)).</p> <p>In Table 13: AC characteristics at 400 kHz (M24M01-R and M24M01-W), Note 1 modified, Note 2 added, t_{XH1XH2}, t_{XL1XL2} and t_{DL1DL2} values modified.</p> <p>In Table 14: AC characteristics at 1 MHz (M24M01-HR), Note 1 modified, Note 3 added, t_{XH1XH2}, t_{XL1XL2} and t_{DL1DL2} values modified.</p> <p>t_{CHDX}, t_{DL1DL2} and t_{DXCX} changed to t_{CHDL}, t_{QL1QL2} and t_{DXCH}, respectively (see Table 13, Table 14 and Figure 13).</p> <p>Table 19: Available M24M01-x products (package, voltage range, frequency, temperature grade) added.</p> <p>Small text changes.</p>
12-Mar-2009	6	<p>WLCSP8 package added (see Figure 3: WLCSP8 connections (bumps side view) and Section 7: Package mechanical data).</p> <p>Section 2.6: Supply voltage (VCC) updated.</p> <p>I_{OL} added to Table 5: Absolute maximum ratings.</p> <p>V_{RES} added to Table 11: DC characteristics (M24M01-R and M24M01-HR) and Table 12: DC characteristics (M24M01-W).</p> <p>ECOPACK text updated.</p>
26-Jun-2009	7	<p>Section : Features updated.</p> <p>NC pin changed to DU in Figure 2: SO connections.</p> <p>Device select code Chip enable address bits updated in Section 2.3.</p> <p>Internal reset threshold modified in Section 2.6.3: Device reset.</p> <p>Figure 6: Maximum Rbus value versus bus parasitic capacitance (Cbus) for an I2C bus at maximum frequency $f_C = 1\text{MHz}$ updated.</p> <p>V_{RES} removed, and I_{CC1} conditions modified in Table 11: DC characteristics (M24M01-R and M24M01-HR), and Table 12: DC characteristics (M24M01-W). V_{RES} removed from Table 12: DC characteristics (M24M01-W).</p> <p>t_{XH1XH2} updated in Table 13: AC characteristics at 400 kHz (M24M01-R and M24M01-W). t_{XH1XH2} updated, and Note 5 updated in Table 14: AC characteristics at 1 MHz (M24M01-HR).</p> <p>Command replaced by instruction in the whole document.</p>

Table 21. Document revision history (continued)

Date	Revision	Changes
02-May-2011	8	<p>Updated Features on page 1.</p> <p>Updated Figure 3: WLCSP8 connections (bumps side view), Figure 5: Maximum R_{bus} value versus bus parasitic capacitance (C_{bus}) for an I2C bus at maximum frequency $f_C = 400$ kHz and Figure 6: Maximum R_{bus} value versus bus parasitic capacitance (C_{bus}) for an I2C bus at maximum frequency $f_C = 1$ MHz.</p> <p>Updated Table 10: DC characteristics (M24M01-R and M24M01-HR).</p> <p>Updated footnote 5 of Table 14: AC characteristics at 1 MHz (M24M01-HR).</p> <p>Modified description of Write Control in Section 3.6: Write operations.</p> <p>Replaced C_L with C_{bus} in Table 7: AC measurement conditions.</p> <p>Changed note 4 about t_{CLQV} in Table 13: AC characteristics at 400 kHz (M24M01-R and M24M01-W).</p>
23-Apr-2012	9	<p>Datasheet split into:</p> <ul style="list-style-type: none"> – M24M01-R, M24M01-DF (this datasheet) for standard products (range 6), – M24M01-125 datasheet for automotive products (range 3).

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